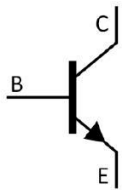


Rev.E Mar.-2016

TO-126F NPN Silicon NPN transistor in a TO-126F Plastic Package.

Low saturation voltage, high DC current gain.

Audio frequency amplifier and switching applications.



PIN1 Emitter PIN 2 Collector PIN 3 Base

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	30	V
Collector Current - Continuous	I_C	5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	10	A
Base Current - Continuous	I_B	2.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C (T_c=25^\circ C)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=30V$ $I_E=0$			0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=6.0V$ $I_C=0$			0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0V$ $I_C=1.0A$	150		600	
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=4.0A$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=1.0A$ $I_B=50mA$		0.07	0.15	V
	$V_{CE(sat)(2)}$	$I_C=2.0A$ $I_B=0.1A$		0.13	0.25	V
	$V_{CE(sat)(3)}$	$I_C=4.0A$ $I_B=0.2A$		0.24	0.50	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2.0A$ $I_B=0.1A$		0.86	1.50	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=50mA$		120		MHz
Reverse Transfer Capacitance	C_{ob}	$V_{CB}=10V$ $f=1.0MHz$		77		pF

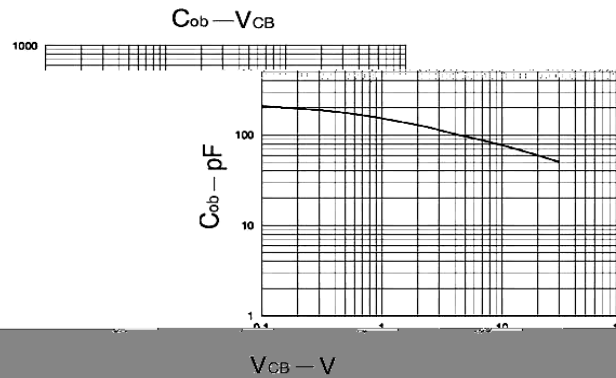
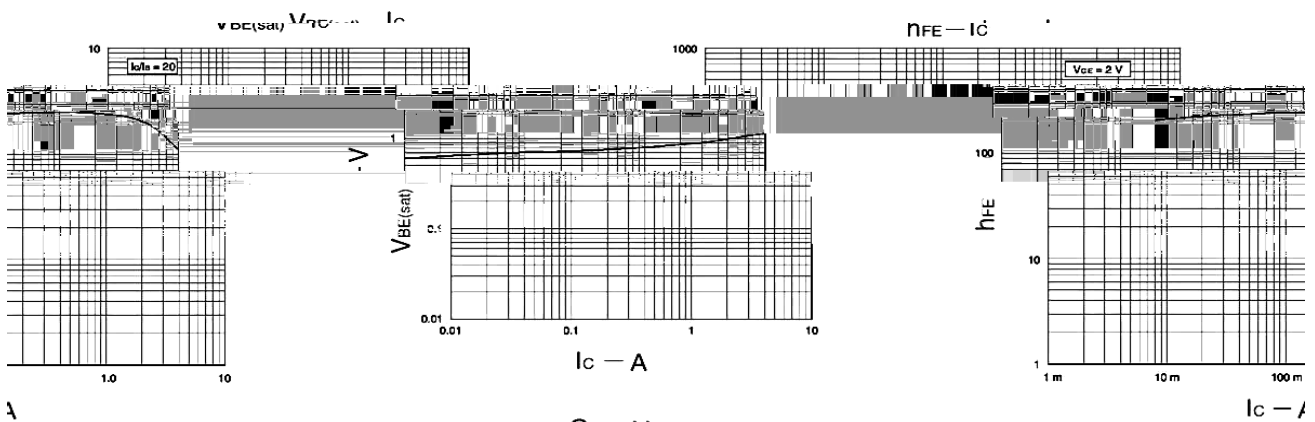
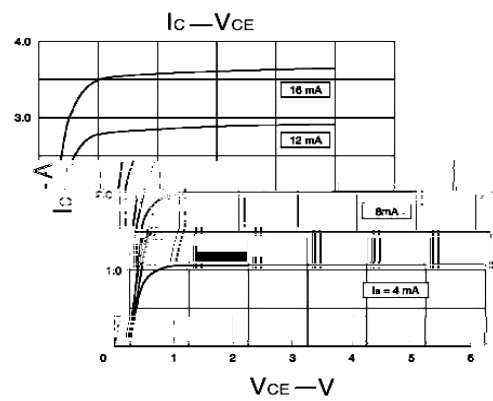
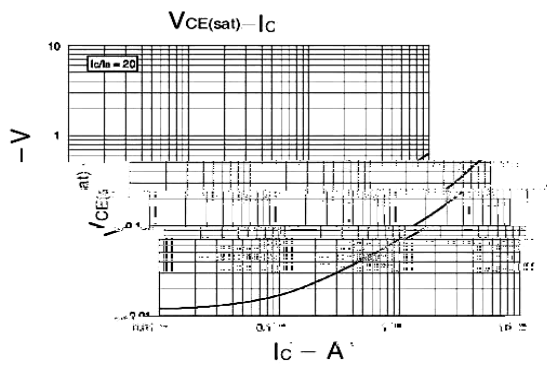
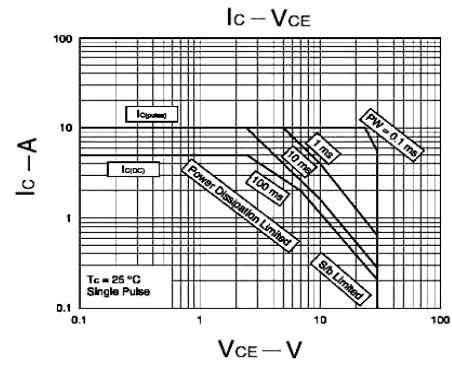
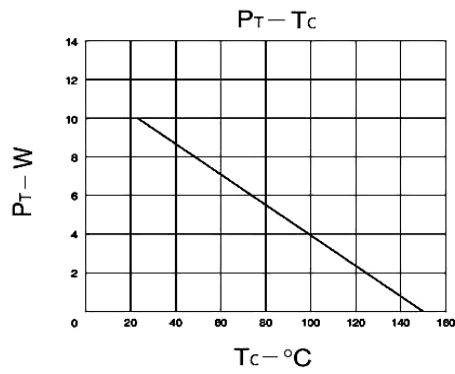
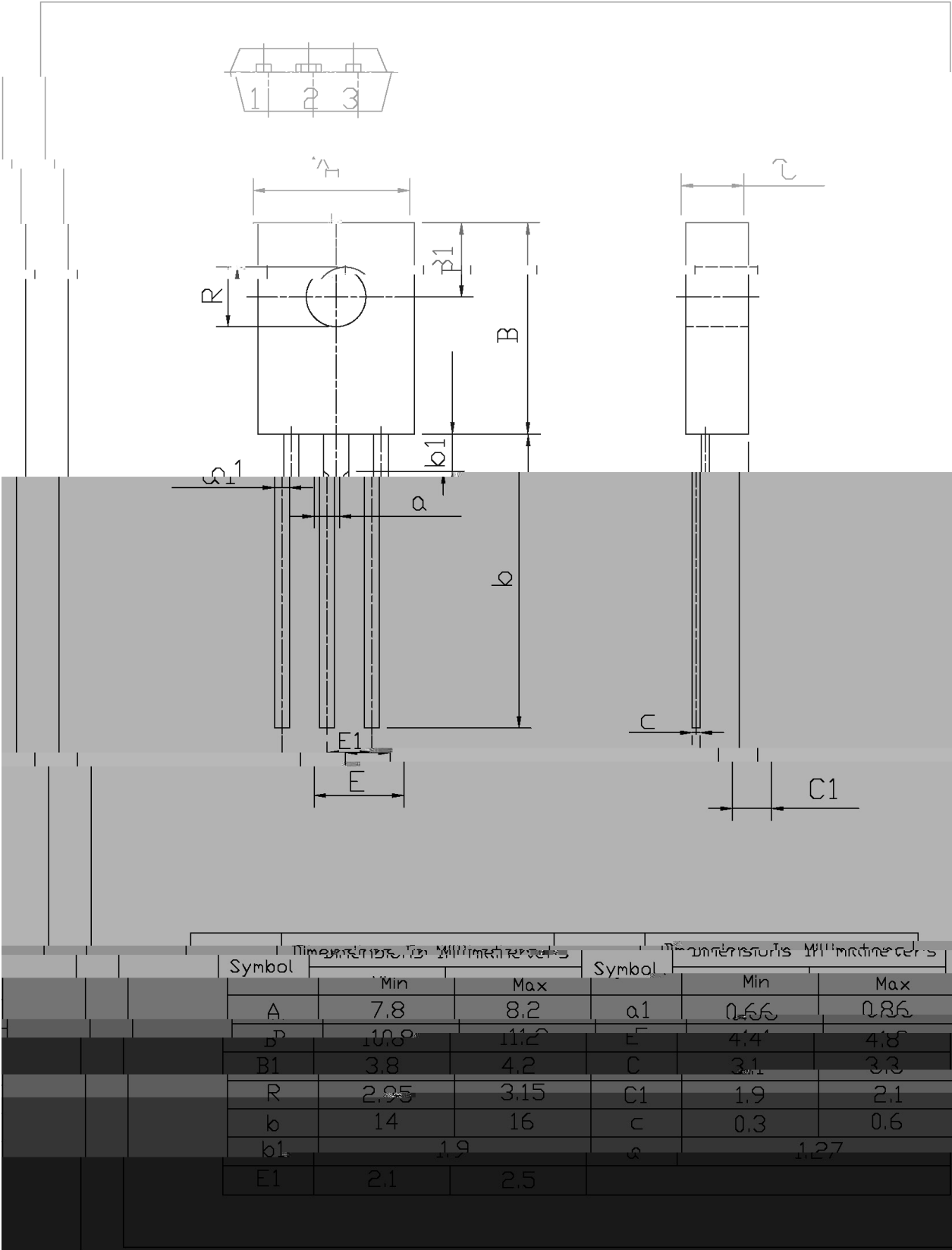
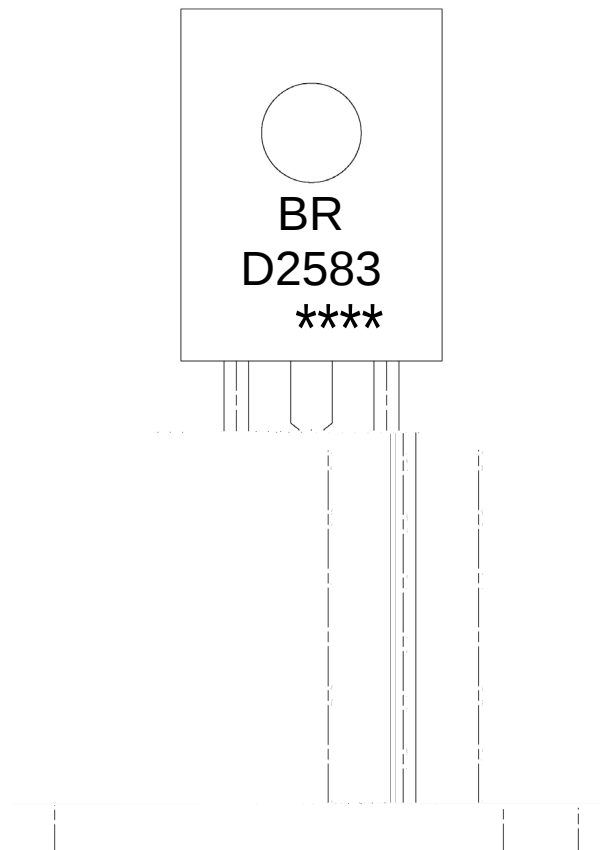


图 1261 单位: mm





BR

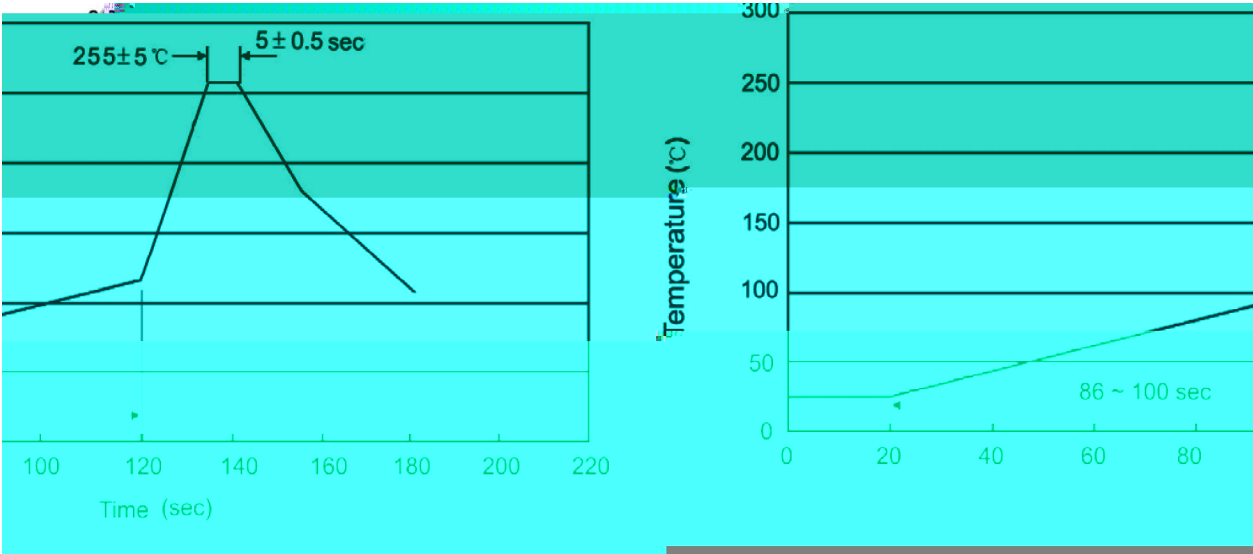
D2583

Note:

BR: Company Code

D2583: Product Type.

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量		Dimension 包装尺寸 (unit: mm ³)
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	